



《风光欣》技术资料

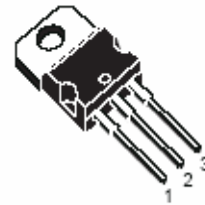
TIP41/A/B/C NPN EPITAXIAL SILICON TRANSISTOR

MEDIUM POWER LINEAR SWITCHING APPLICATIONS

*Complement to TIP42/42A/42B/42C

ABSOLUTE MAXIMUM RATINGS($T_A=25$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage:TIP41 TIP41A TIP41B TIP41C	V_{CB0}	40	V
		60	V
		80	V
		100	V
Collector-Emitter Voltage:TIP41 TIP41A TIP41B TIP41C	V_{CE0}	40	V
		60	V
		80	V
		100	V
Emitter -Base Voltage	V_{EB0}	5	V
Collector Current(DC)	I_C	6	A
Collector Current(Pulse)	I_C	10	A
Base Current	I_B	2	A
Collector Dissipation($T_c=25$ C)	P_C	65	W
Collector Dissipation($T_a=25$ C)	P_C	2	W
Junction Temperature	T_J	150	
Storage Temperature	T_{STG}	-65 ~150	



TO-220

1.Base 2.Collector 3.Emitter

ELECTRICAL CHARACTERISTICS($T_A=25$)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Emitter Sustaining Voltage:TIP41 TIP41A TIP41B TIP41C	$V_{CE0(SUS)}$	$I_C=30mA, I_B=0$	40			V
			60			V
			80			V
			100			V
Collector Cut-off Current : TIP41/TIP41A TIP41B/TIP41C	I_{CE0}	$V_{CE}= 30V, I_B=0$			700	μA
		$V_{CE}= 60V, I_B=0$			700	μA
Collector Cut-off Current : TIP41 TIP41A TIP41B TIP41C	I_{CES}	$V_{CE}= 40V, V_{EB}=0$			400	μA
		$V_{CE}= 60V, V_{EB}=0$			400	
		$V_{CE}= 80V, V_{EB}=0$			400	
		$V_{CE}= 100V, V_{EB}=0$			400	
DC Current Gain	H_{FE1}	$V_{CE}= 4V, I_C= 0.3A$	30			
	H_{FE2}	$V_{CE}= 4V, I_C= 3A$	15		75	
Emitter-Cutoff Current	I_{EB0}	$V_{EB}= 5V, I_C=0$			1	mA
Base-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C= 6A, I_B= 600mA$			1.5	V
Base-Emitter On Voltage	$V_{BE(on)}$	$V_{CE}= 4V, I_C= 6A$			2.0	V
Current Gain-Bandwidth Product	f_T	$V_{CE}= 10V, I_C= 500mA$	3			MHz